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Team Nexperia



150 V, 1 A NPN high-voltage low VCEsat BISS transistor
10 January 2017 Product data sheet

## 1. General description

NPN high-voltage low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9115TLH

#### 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- Small SMD plastic package
- AEC-Q101 qualified

## 3. Applications

- Power management
- LCD backlighting
- · LED driver for LED chain module
- · Switch Mode Power Supply (SMPS)

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	150	V
I <sub>C</sub>	collector current		-	-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	2	Α
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C	70	-	300	



# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	Е	emitter		В
3	С	collector	TO-236AB (SOT23)	E sym123

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PBHV8115TLH	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PBHV8115TLH	FB%

[1] % = placeholder for manufacturing site code

2/14

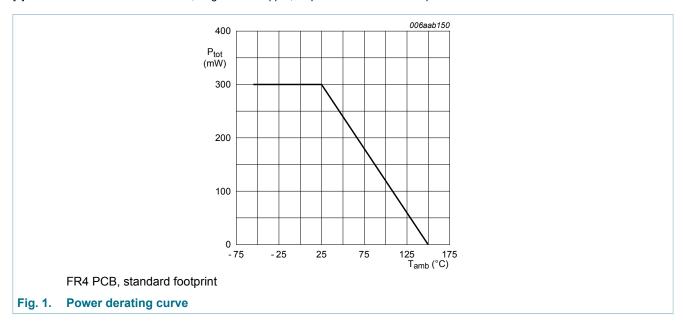
# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	400	V
$V_{CEO}$	collector-emitter voltage	open base		-	150	V
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	200	V
$V_{EBO}$	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	2	Α
I <sub>BM</sub>	peak base current			-	400	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



3 / 14

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

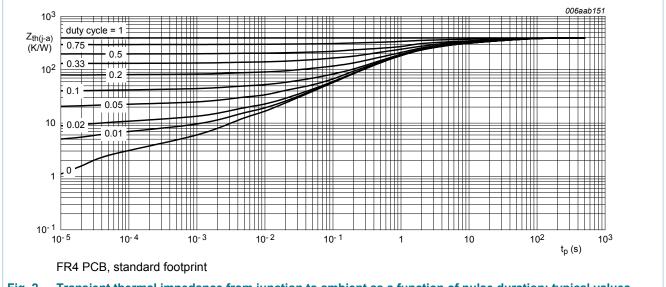


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	M	n Typ	Max	Unit
сво	collector-base cut-off	V <sub>CB</sub> = 120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	10	μA
CES	collector-emitter cut-off current	V <sub>CE</sub> = 120 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
EBO	emitter-base cut-off current	$V_{EB}$ = 4 V; $I_C$ = 0 A; $T_{amb}$ = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; $T_{amb}$ = 25 °C	70	-	300	
		$V_{CE}$ = 10 V; $I_{C}$ = 100 mA; $T_{amb}$ = 25 °C	60	-	300	
		$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02 ; $T_{amb}$ = 25 °C	50	-	300	
		$V_{CE}$ = 10 V; $I_{C}$ = 1 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02 ; $T_{amb}$ = 25 °C	10	-	-	
V <sub>CEsat</sub>	collector-emitter	$I_C$ = 100 mA; $I_B$ = 10 mA; $T_{amb}$ = 25 °C	-	-	60	mV
	saturation voltage	$I_C$ = 100 mA; $I_B$ = 20 mA; $T_{amb}$ = 25 °C	-	-	50	mV
		$I_C$ = 1 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	350	mV
V <sub>BEsat</sub>	base-emitter saturation voltage		-	-	1.2	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 6 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 0.1 mA;	-	10	-	ns
t <sub>r</sub>	rise time	$I_{Boff}$ = -0.1 mA; $T_{amb}$ = 25 °C	-	565	-	ns
t <sub>on</sub>	turn-on time	V <sub>CC</sub> = 6 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 0.1 A;	-	575	-	ns
t <sub>s</sub>	storage time	I <sub>Boff</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	-	1530	-	ns
t <sub>f</sub>	fall time		-	700	-	ns
t <sub>off</sub>	turn-off time		-	2230	-	ns
fт	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	30	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 20 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C	-	6	-	pF
C <sub>e</sub>	emitter capacitance	V <sub>EB</sub> = 0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	150	-	pF

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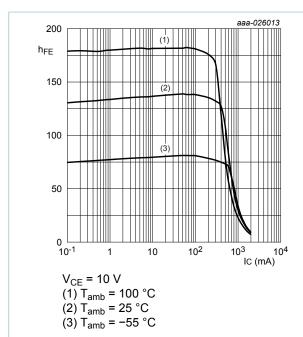


Fig. 3. DC current gain as a function of collector current; typical values

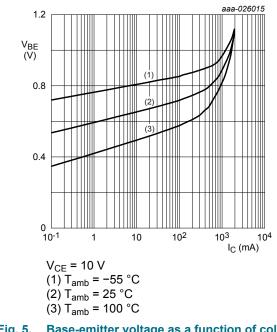


Fig. 5. Base-emitter voltage as a function of collector current; typical values

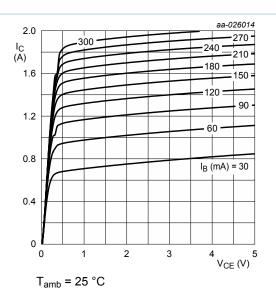
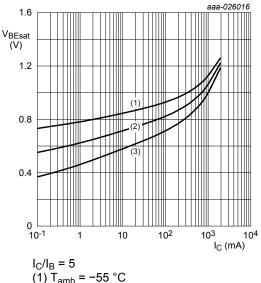


Fig. 4. Collector current as a function of collectoremitter voltage; typical values

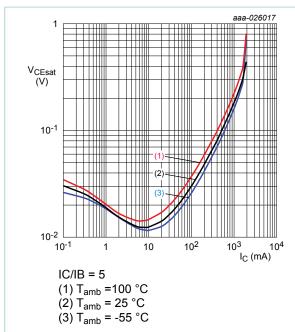


I<sub>C</sub>/I<sub>B</sub> = 5 (1) T<sub>amb</sub> = -55 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

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Collector-emitter saturation voltage as a Fig. 7. function of collector current; typical values

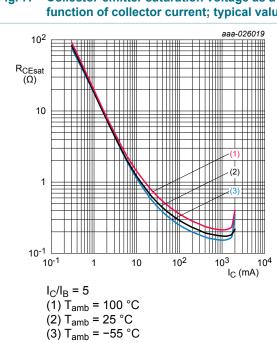


Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values

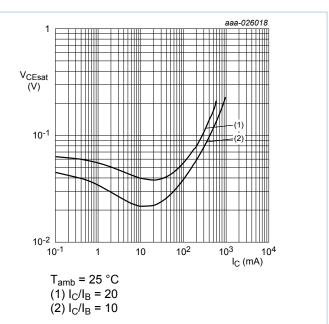


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

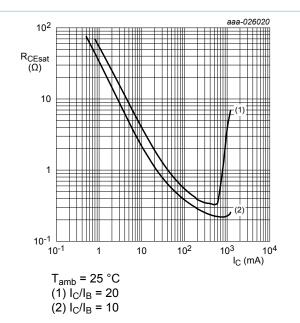
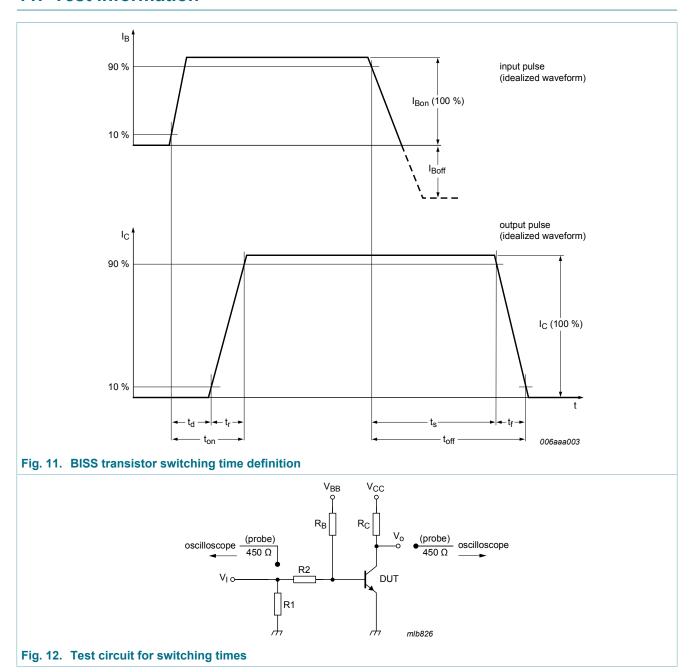


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

7 / 14

### 11. Test information



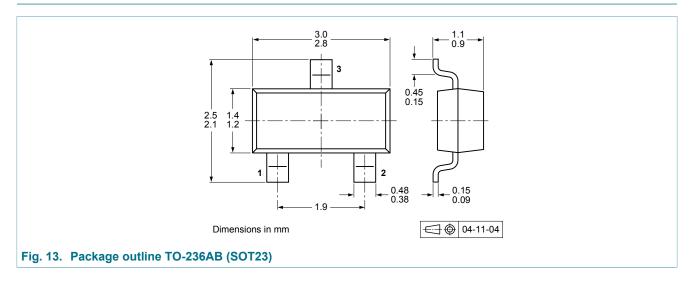
#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

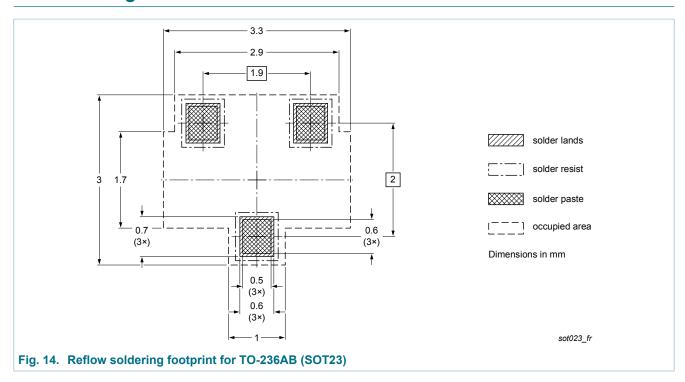
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150 V, 1 A NPN high-voltage low VCEsat BISS transistor

## 12. Package outline

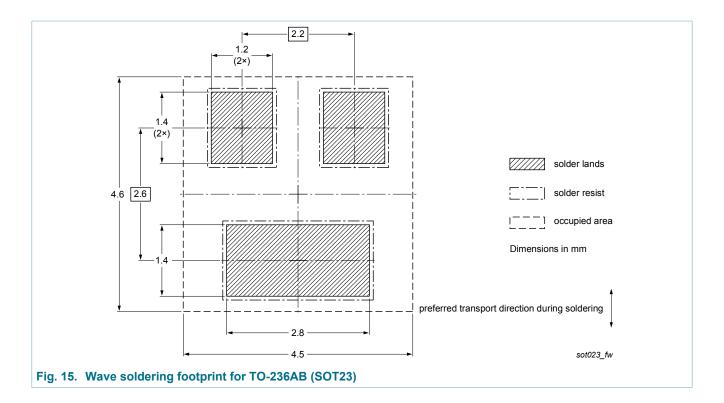


## 13. Soldering



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## 150 V, 1 A NPN high-voltage low VCEsat BISS transistor



# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8115TLH v.1	2017010	Product data sheet	-	-

# 15. Legal information

#### **Data sheet status**

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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## PBHV8115TLH

### 150 V, 1 A NPN high-voltage low VCEsat BISS transistor

## 16. Contents

General description	1
Features and benefits	1
Applications	1
Quick reference data	1
Pinning information	2
Ordering information	2
. Characteristics	5
. Test information	8
Package outline	g
<del>-</del>	
-	
	General description Features and benefits Applications Quick reference data Pinning information Ordering information Marking Limiting values Thermal characteristics Characteristics Test information Package outline Soldering Revision history Legal information

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